Dedicated to the memory of Prof. M. Sheinkman effect of ultrasonic treatment on the defect structure of the Si-SiO2 system
Kropman, Daniel; Dolgov, Sergei; Onufrijevs, Pavels; Dauksta, Edvins Gettering and Defect Engineering in Semiconductor Technology XV 2014 / p. 352-357 : ill https://doi.org/10.4028/www.scientific.net/SSP.205-206.352 Conference proceedings at Scopus Article at Scopus Conference proceedings at WOS Article at WOS

Low-K factor of SiO2 layer on Si irradiated by YAG:Nd laser
Medvid, A.; Onufrijevs, Pavels; **Mellikov, Enn**; **Kropman, Daniel**; Muktepavela, F.; Bakradze, G. Journal of non-crystalline solids 2007 / p. 703-707 : ill https://www.sciencedirect.com/science/article/pii/S0022309306014116

Stress relaxation mechanism by strain in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; **Mellikov, Enn**; Kärner, Tiit; Laas, Tõnu; Medvid, Arthur; Onufrijevs, Pavels; Dauksta, Edvins Solid state phenomena 2011 / p. 259-262 https://globaljournals.org/GJSFR_Volume17/1-Stresses-Relaxation-Mechanism.pdf

Understanding and control of stress at Si-SiO2 interface
Kropman, Daniel; Seeman, Viktor; Medvids, Arturs; Onufrijevs, Pavels; Vitusevich, Svetlana; **Mikli, Valdek** Key engineering materials 2020 / p. 291−296 https://doi.org/10.4028/www.scientific.net/KEM.850.291 Journal metrics at Scopus Article at Scopus